

4A, 300V N-CHANNEL POWER MOSFET

GENERAL DESCRIPTION

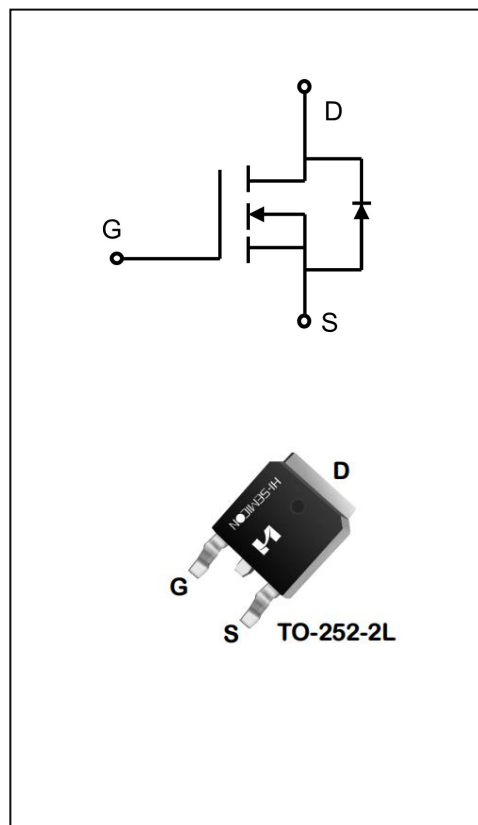
These N-Channel enhancement mode power field effect transistors are produced using Hi-semicon's proprietary, planar stripe, VDMOS technology.

Features

- ◆ $V_{DS}=300V, I_D=4A$
- ◆ $R_{DS(ON)}$
 TYP: $1.3\Omega @ V_{GS}=10V$
 MAX: 1.6Ω

Applications

- ◆ Power faction correction (PFC)
- ◆ Switched mode power supplies (SMPS)
- ◆ Uninterruptible power supply (UPS)
- ◆ LED lighting power



ORDERING INFORMATION

Part No.	Package	Marking	Material	Packing
SFD4N30	TO-252-2L	SFD4N30	Pb free	Reel

ABSOLUTE MAXIMUM RATINGS (T_J=25°C unless otherwise noted)

Characteristics	Symbol	Ratings	Unit
Drain-Source Voltage	V _{DS}	400	V
Gate-Source Voltage	V _{GS}	±30	V
Drain Current	I _D	T _C = 25°C	4
		T _C = 100°C	3.2
Drain Current Pulsed (Note 1)	I _{DM}	16	A
Power Dissipation(T _C =25°C) -Derate above 25°C	P _D	57	W
		0.42	W/°C
Single Pulsed Avalanche Energy (Note 2)	E _{AS}	101.2	mJ
Operation Junction Temperature Range	T _J	-55~+150	°C
Storage Temperature Range	T _{stg}	-55~+150	°C
Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	TL	300	°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	MAX	Unit
Thermal Resistance, Junction-to-Case	R _{θJC}	2.62	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	62.0	°C/W

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
Drain -Source Breakdown Voltage	B _{VDS}	V _{GS} =0V, I _D =250μA	300	350	--	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =300V, V _{GS} =0V	--	--	100	nA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =30V, V _{DS} =0V	--	--	100	nA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =-30V, V _{DS} =0V	--	--	-100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{GS} = V _{DS} , I _D =250μA	2.0	3.1	4.0	V
Static Drain- Source On State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =2.0A	--	1.3	1.6	Ω
Dynamic Characteristics						
Gate Resistance	R _g	V _{GS} =0V; f=1.0MHZ	--	18	--	Ω
Input Capacitance	C _{iss}	V _{DS} =100V V _{GS} =0V f=1.0MHZ	--	250	--	pF
Output Capacitance	C _{oss}		--	15.5	--	
Reverse Transfer Capacitance	C _{rss}		--	4.4	--	
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	V _{DD} =180V R _G =25Ω I _D =4A (Note 3.4)	--	16.8	--	ns
Turn-on Rise Time	t _r		--	32.4	--	

Turn-off Delay Time	$t_{d(off)}$	$V_{DD}=180V$ $R_G=25\Omega$	--	26.7	--	ns
Turn-off Fall Time	t_f	$I_D=4A$ (Note 3.4)	--	25.1	--	
Total Gate Charge	Q_g	$V_{DS}=240V, I_D=4A$ $V_{GS}=10V$ (Note 3.4)	--	9.34	--	nc
Gate-Source Charge	Q_{gs}		--	1.17	--	
Gate-Drain Charge	Q_{gd}		--	6.57	--	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Continuous Source Current	I_S	Integral Reverse P-N Junction Diode in the MOSFET	--	--	4	A
Pulsed Source Current	I_{SM}		--	--	16	
Diode Forward Voltage	V_{SD}	$I_S=4A, V_{GS}=0V$	--	0.85	1.4	V
Reverse Recovery Time	T_{rr}	$I_F=4A, V_R=500V,$ $dI_F/dt=100A/\mu S$	--	417	--	ns
Reverse Recovery Charge	Q_{rr}		--	0.61	--	μC

1. Pulse width limited by maximum junction temperature
2. $L=10mH, I_{AS}=4.0A, V_{DD}=100V, V_G=10V, R_G=25\Omega,$ starting $T_J=25^\circ C$
3. Pulse Test: Pulse width $\leq 300\mu s,$ Duty cycle $\leq 2\%$
4. Essentially independent of operating temperature

Typical Performance Characteristics

Figure 1. On-Region Characteristics

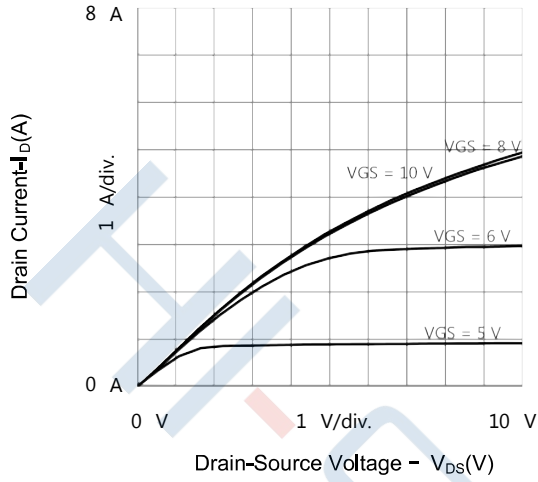


Figure 2. Transfer Characteristics

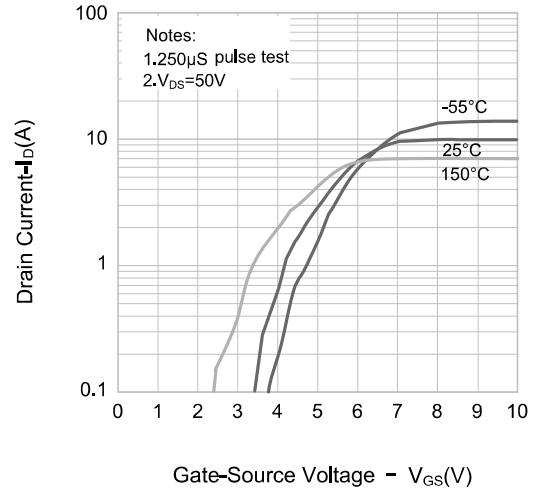


Figure 3. On-Resistance Variation vs. Drain-Current, Gate Voltage

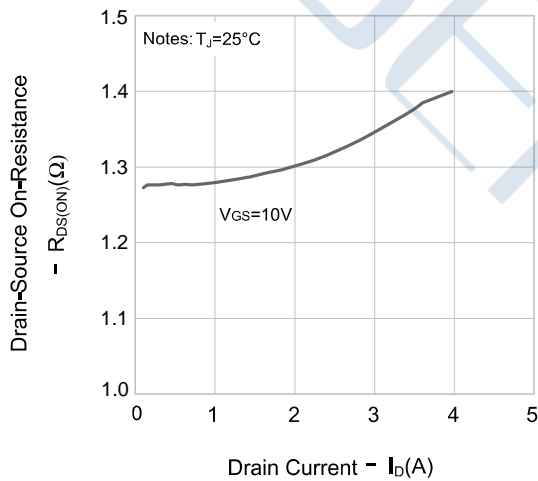


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

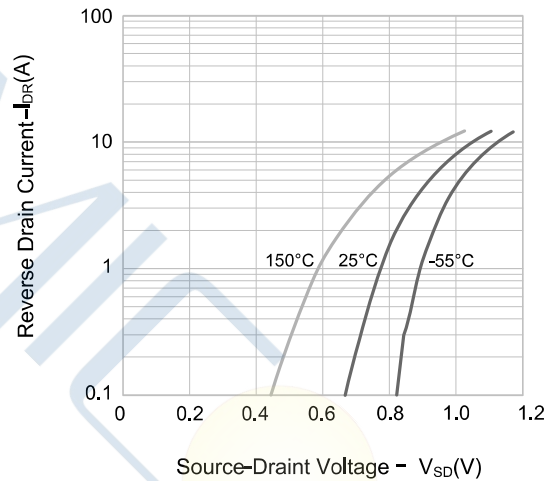


Figure 5. Capacitance Characteristics

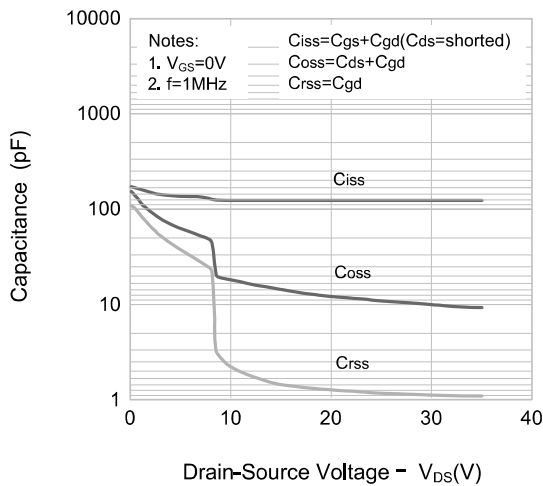
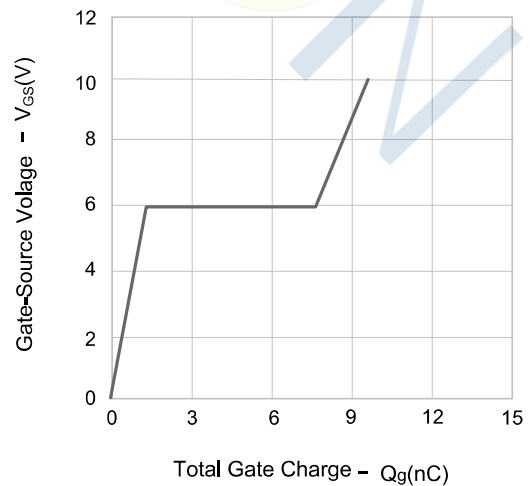


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics

Figure 7. Breakdown Voltage Variation vs. Temperature

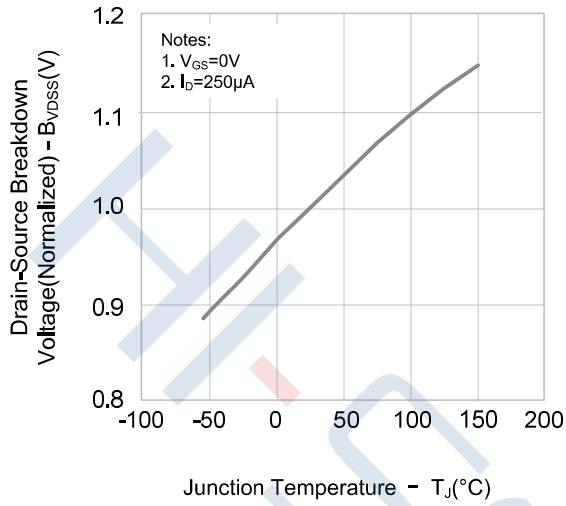


Figure 8. On-resistance Variation vs. Temperature

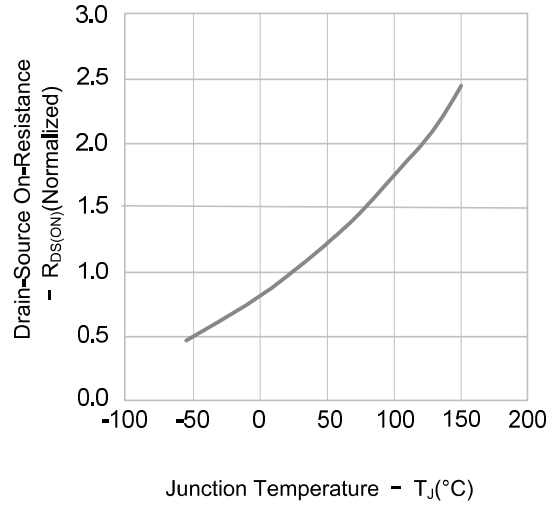


Figure 9. Max. Safe Operating Area

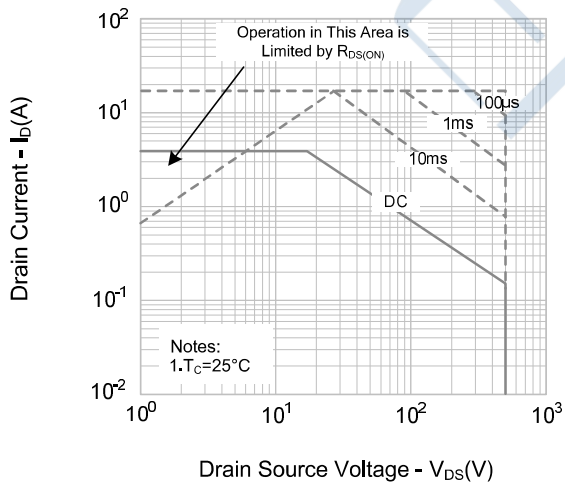
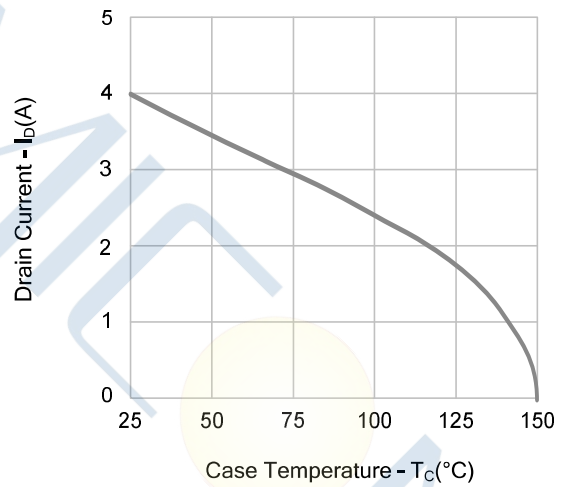
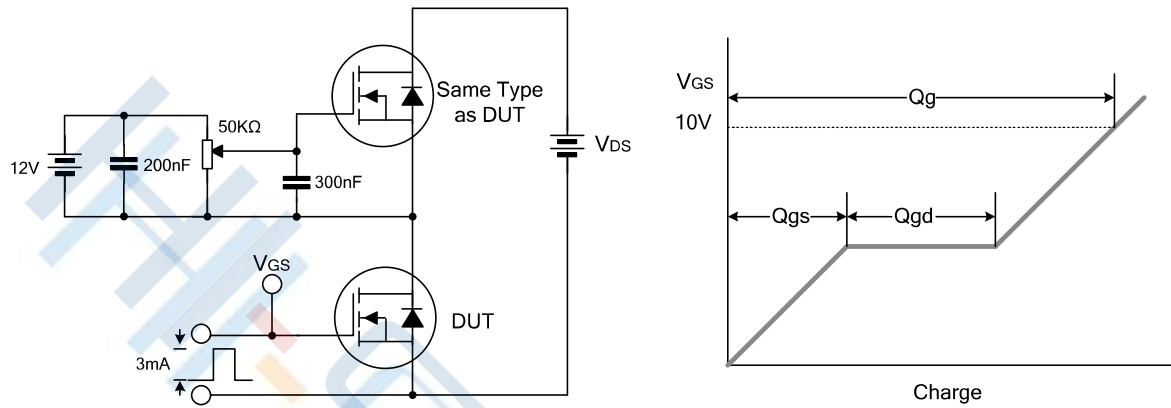


Figure 10. Maximum Drain Current vs. Case Temperature

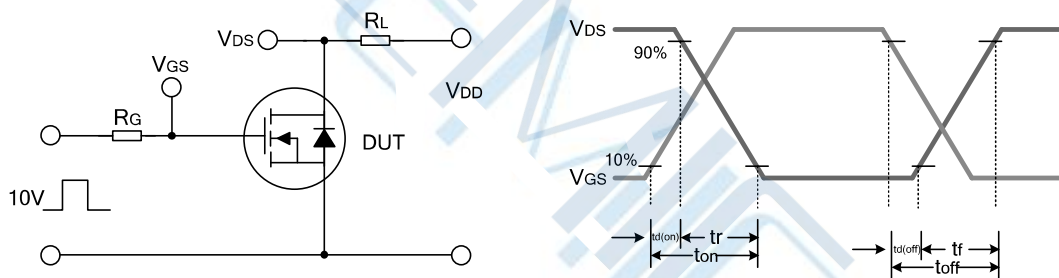


Test Circuit

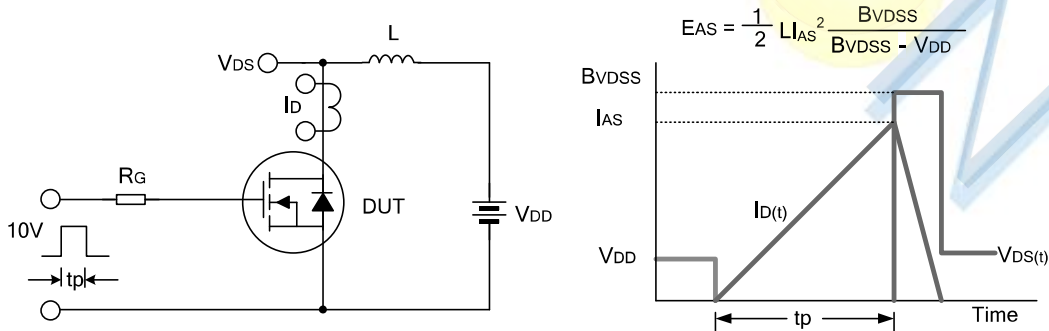
Gate Charge Test Circuit & Waveform



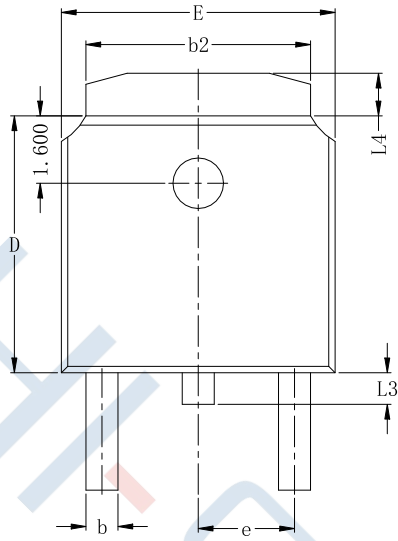
Resistive Switching Test Circuit & Waveform



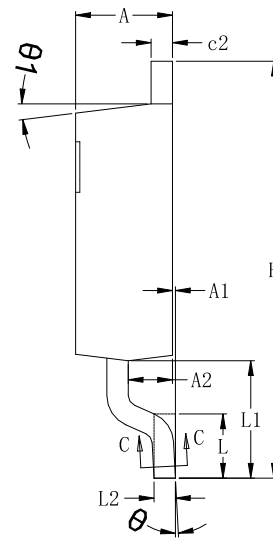
Undamped Inductive Switching Test Circuit & Waveform



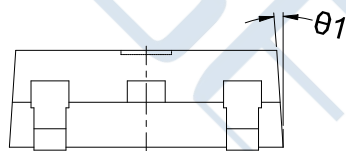
Package Dimensions of TO-252-2L



TOP VIEW



SIDE VIEW (Right)



SIDE VIEW (Front)

DIM SYMBOL	MIN.	NOM.	MAX.
A	2.200	2.300	2.400
A1	0.000	0.070	0.130
A2	0.950	1.050	1.150
b	0.700	0.800	0.900
b1	0.660	0.760	0.860
b2	5.134	5.334	5.534
c	0.448	0.548	0.648
c1	0.458	0.508	0.558
c2	0.448	0.548	0.648
D	6.000	6.100	6.200
D2	5.372	5.572	5.772
E	6.400	6.500	6.600
E2	4.900	5.100	5.300
e	2.286 BSC.		
H	9.700	9.900	10.100
L	1.380	1.525	1.725
L1	2.588	2.788	2.988
L2	0.508 BSC.		
L3	0.600	0.750	0.950
L4	0.812	1.012	1.212
theta	1°	3°	5°
theta1	6°	7°	8°

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